

STPS40M60C

High efficiency 60 V power Schottky rectifier

Features

- High current capability
- Avalanche rated
- Low forward voltage drop
- Low leakage current
- High frequency operation

Description

This dual diode Schottky rectifier is suited for high frequency switch mode power supply.

Packaged in TO-220AB, I²PAK and D²PAK, this device is particularly suited for use in notebook, game station and desktop adapters, providing these applications with a good efficiency at both low and high load.

Table 1. Device summary

| Symbol | Value |
|----------------------|----------|
| I _{F(AV)} | 2 x 20 A |
| V _{RRM} | 60 V |
| T _j (max) | 150 °C |
| V _F (typ) | 385 mV |

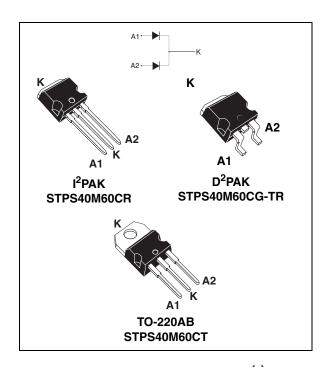
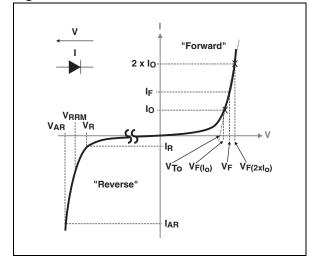


Figure 1. Electrical characteristics^(a)



V_{ARM} and I_{ARM} must respect the reverse safe operating area defined in *Figure 13*. V_{AR} and I_{AR} are pulse measurements (t_p < 1 μs). V_R, I_R, V_{RRM} and V_F, are static characteristics

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1 Characteristics

Table 2. Absolute ratings (limiting values, per diode, at $T_{amb} = 25$ °C unless otherwise specified)

| Symbol | Parameter | | | | | Unit |
|---------------------------------|--|--|--|-------------|-----|------|
| V _{RRM} | Repetitive peak reverse voltage | | | 60 | V | |
| I _{F(RMS)} | Forward rms current | | | | 30 | Α |
| I _{F(AV)} | Average forward current, $\delta = 0.5$ $ T_c = 130 ^{\circ}\text{C} $ Per diode $ T_c = 120 ^{\circ}\text{C} $ Per device | | | 20 40 | Α | |
| I _{FSM} | Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$ | | | | 220 | Α |
| P _{ARM} ⁽¹⁾ | Repetitive peak avalanche power $T_j = 25$ °C, $t_p = 1$ µs | | | 23000 | W | |
| V _{ARM} ⁽²⁾ | Maximum repetitive peak avalanche voltage $t_p < 1~\mu s,~T_j < 150~^{\circ}\text{C},~I_{AR} < 86.3~\text{A}$ | | | 80 | V | |
| T _{stg} | Storage temperature range | | | -65 to +175 | °C | |
| Tj | Maximum operating junction temperature ⁽³⁾ | | | | 150 | °C |

For temperature or pulse time duration deratings, please refer to figure 3 and 4. More details regarding the avalanche energy measurements and diode validation in the avalanche are provided in the application notes AN1768 and AN2025.

Table 3. Thermal parameters

| Symbol | Parameter | Value | Unit | |
|----------------------|------------------|----------|------|--------|
| В | Junction to case | er diode | 1.40 | °C/W |
| R _{th(j-c)} | | total | 0.95 | J 5/VV |
| R _{th(c)} | Coupling | 0.50 | °C/W | |

When the two diodes 1 and 2 are used simultaneously:

$$\Delta T_i$$
(diode 1) = P(diode 1) x R_{th(j-c)}(Per diode) + P(diode 2) x R_{th(c)}

^{2.} See Figure 13

^{3.} $\frac{dPtot}{dT_i} < \frac{1}{Rth(j-a)}$ condition to avoid thermal runaway for a diode on its own heatsink

STPS40M60C Characteristics

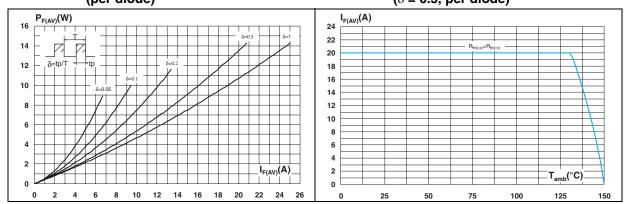
Table 4. Static electrical characteristics (per diode)

| Symbol | Parameter | Test conditions | | Min. | Тур. | Max. | Unit |
|-------------------------------|--|-------------------------|-----------------------|-------|-------|-------|------|
| I _B ⁽¹⁾ | L (1) Payarras la alvana ayyrant | T _j = 25 °C | V _B = 60 V | - | 25 | 110 | μΑ |
| 'R`´ | Reverse leakage current | T _j = 125 °C | v _R = 60 v | - | | 85 | mA |
| | | T _j = 25 °C | I _F = 5A | - | 0.430 | 0.460 | |
| | T _j = 125 °C | IF = 5A | - | 0.325 | 0.355 | | |
| | V _F ⁽²⁾ Forward voltage drop | T _j = 25 °C | I _F = 10 A | - | 0.470 | 0.505 | |
| v (2) | | T _j = 125 °C |] IF = 10 A | - | 0.385 | 0.435 | V |
| VF` | | T _j = 25 °C | I _F = 20 A | - | 0.540 | 0.595 | V |
| | T _j = 125 °C | IF = 20 A | - | 0.475 | 0.535 | | |
| | | T _j = 25 °C | I _F = 40 A | - | 0.645 | 0.730 | |
| | | T _j = 125 °C |] IF = 40 A | - | 0.605 | 0.675 | |

- 1. Pulse test: t_p = 5 ms, δ < 2 %
- 2. Pulse test: t_p = 380 μ s, δ < 2 %

To evaluate the conduction losses use the following equation: $P = 0.395 \text{ x } I_{F(AV)} + 0.007 \text{ x } I_{F}^{2}_{(RMS)}$

Figure 2. Average forward power dissipation Figure 3. Average forward current versus average forward current ambient temperature (per diode) (δ = 0.5, per diode)



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Figure 4. Normalized avalanche power derating versus pulse duration

Figure 5. Normalized avalanche power derating versus junction temperature

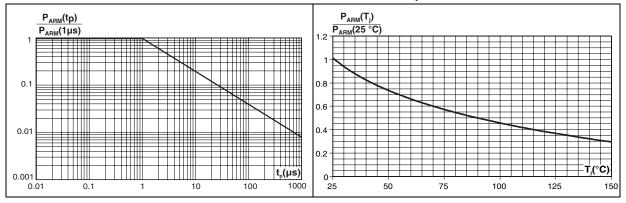


Figure 6. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

Figure 7. Relative thermal impedance junction to case versus pulse duration

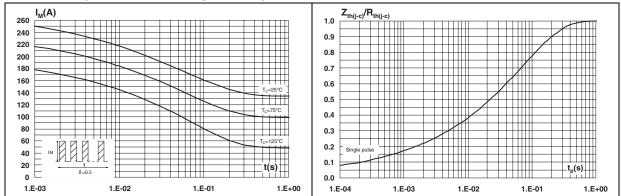
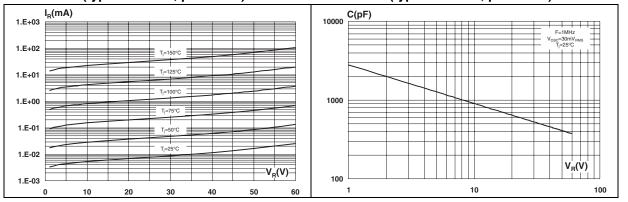


Figure 8. Reverse leakage current versus reverse voltage applied (typical values, per diode)

Figure 9. Junction capacitance versus reverse voltage applied (typical values, per diode)

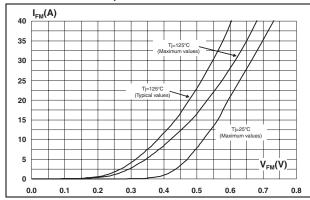


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STPS40M60C Characteristics

Figure 10. Forward voltage drop versus forward current (per diode, low level)

Figure 11. Forward voltage drop versus forward current (per diode, high level)



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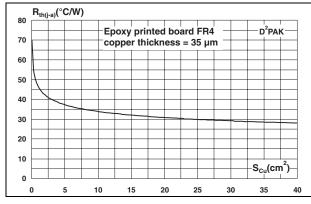
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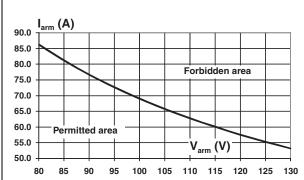
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Figure 12. Thermal resistance junction to ambient versus copper surface under tab for D²PAK

Figure 13. Reverse safe operating area $(t_p < 1 \mu s \text{ and } T_j < 150 \,^{\circ}\text{C})$



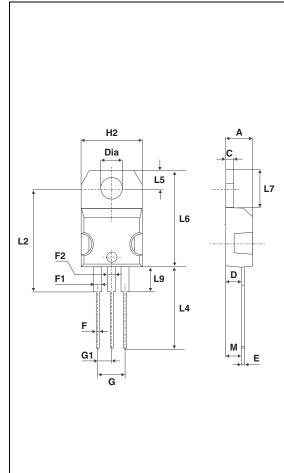


2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)
- Recommended torque value: 0.4 to 0.6 N⋅m

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Table 5. TO-220AB dimensions



| | Dimensions | | | |
|------|-------------|-------|-------|--------|
| Ref. | Millimeters | | Inc | hes |
| | Min. | Max. | Min. | Max. |
| Α | 4.40 | 4.60 | 0.173 | 0.181 |
| С | 1.23 | 1.32 | 0.048 | 0.051 |
| D | 2.40 | 2.72 | 0.094 | 0.107 |
| Е | 0.49 | 0.70 | 0.019 | 0.027 |
| F | 0.61 | 0.88 | 0.024 | 0.034 |
| F1 | 1.14 | 1.70 | 0.044 | 0.066 |
| F2 | 1.14 | 1.70 | 0.044 | 0.066 |
| G | 4.95 | 5.15 | 0.194 | 0.202 |
| G1 | 2.40 | 2.70 | 0.094 | 0.106 |
| H2 | 10 | 10.40 | 0.393 | 0.409 |
| L2 | 16.4 | Тур. | 0.645 | 5 Тур. |
| L4 | 13 | 14 | 0.511 | 0.551 |
| L5 | 2.65 | 2.95 | 0.104 | 0.116 |
| L6 | 15.25 | 15.75 | 0.600 | 0.620 |
| L7 | 6.20 | 6.60 | 0.244 | 0.259 |
| L9 | 3.50 | 3.93 | 0.137 | 0.154 |
| М | 2.6 Typ. | | 0.102 | 2 Тур. |
| Dia. | 3.75 | 3.85 | 0.147 | 0.151 |

Table 6. D²PAK dimensions

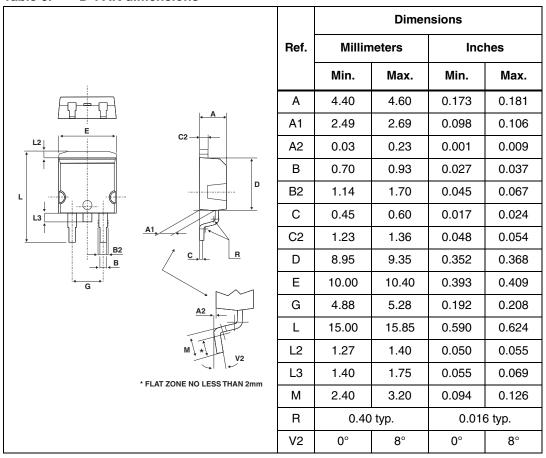
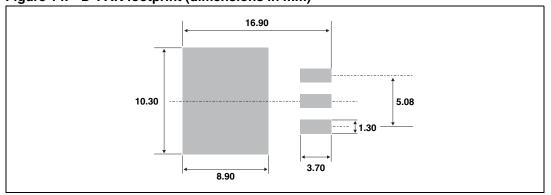
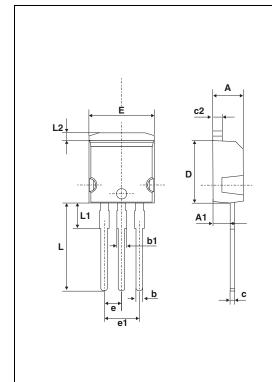


Figure 14. D²PAK footprint (dimensions in mm)



Package information STPS40M60C

Table 7. I²PAK dimensions



| | Dimensions | | | | |
|------|-------------|-------|--------|-------|--|
| Ref. | Millimeters | | Inches | | |
| | Min. | Max. | Min. | Max. | |
| Α | 4.40 | 4.60 | 0.173 | 0.181 | |
| A1 | 2.40 | 2.72 | 0.094 | 0.107 | |
| b | 0.61 | 0.88 | 0.024 | 0.035 | |
| b1 | 1.14 | 1.70 | 0.044 | 0.067 | |
| С | 0.49 | 0.70 | 0.019 | 0.028 | |
| c2 | 1.23 | 1.32 | 0.048 | 0.052 | |
| D | 8.95 | 9.35 | 0.352 | 0.368 | |
| е | 2.40 | 2.70 | 0.094 | 0.106 | |
| e1 | 4.95 | 5.15 | 0.195 | 0.203 | |
| Е | 10 | 10.40 | 0.394 | 0.409 | |
| L | 13 | 14 | 0.512 | 0.551 | |
| L1 | 3.50 | 3.93 | 0.138 | 0.155 | |
| L2 | 1.27 | 1.40 | 0.050 | 0.055 | |

3 Ordering information

Table 8. Ordering information

| Order code | Marking | Package | Weight | Base qty | Delivery mode |
|----------------|-------------|--------------------|--------|----------|---------------|
| STPS40M60CT | STPS40M60CT | TO-220AB | 2.2 g | 50 | Tube |
| STPS40M60CR | STPS40M60CR | I ² PAK | 1.6 g | 50 | Tube |
| STPS40M60CG-TR | STPS40M60CG | D ² PAK | 1.5 g | 1000 | Tape and reel |

4 Revision history

Table 9. Revision history

| Date | Revision | Changes |
|-------------|----------|--------------|
| 11-May-2011 | 1 | First issue. |

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